ABSTRACT

METHOD FOR MANUFACTURING THE SAME

The invention provides a method for carrying out a heat treatment required during the manufacture of a thin film transistor (TFT) at relatively low temperatures. In this method, in a heating step in which at least a portion of a silicon-based semiconductor layer is crystallized, a silicide is formed in a source region and a drain region in the semiconductor layer. A TFT according to the invention includes a silicon-based semiconductor layer having a channel region, a source region and a drain region being so disposed as to sandwich the channel region, a source electrode electrically connected to the source region, a drain electrode electrically connected to the drain region, and a gate electrode insulated from the source electrode and the drain electrode, and the source region and the drain region contains a silicide.

Figure 1



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